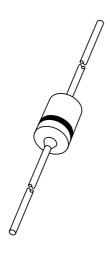
## DISCRETE SEMICONDUCTORS

# DATA SHEET



1N4148; 1N4448 High-speed diodes

Product data sheet Supersedes data of 2002 Jan 23

2004 Aug 10



### **High-speed diodes**

1N4148; 1N4448

#### **FEATURES**

 Hermetically sealed leaded glass SOD27 (DO-35) package

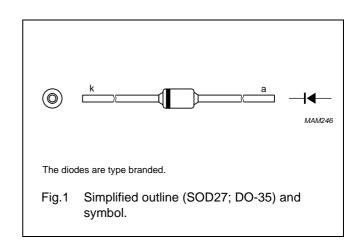
- High switching speed: max. 4 ns
- · General application
- Continuous reverse voltage: max. 100 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 450 mA.

### **APPLICATIONS**

· High-speed switching.

### **DESCRIPTION**

The 1N4148 and 1N4448 are high-speed switching diodes fabricated in planar technology, and encapsulated in hermetically sealed leaded glass SOD27 (DO-35) packages.



### **MARKING**

TYPE NUMBER	MARKING CODE
1N4148	1N4148PH or 4148PH
1N4448	1N4448

### **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE		
TIPE NOWIBER	NAME	NAME DESCRIPTION	
1N4148	_	hermetically sealed glass package; axial leaded; 2 leads	SOD27
1N4448			

# High-speed diodes

1N4148; 1N4448

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>RRM</sub>	repetitive peak reverse voltage		_	100	V
V <sub>R</sub>	continuous reverse voltage		_	100	V
IF	continuous forward current	see Fig.2; note 1	_	200	mA
I <sub>FRM</sub>	repetitive peak forward current		_	450	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; $T_j = 25$ °C prior to surge; see Fig.4			
		t = 1 μs	_	4	Α
		t = 1 ms	_	1	Α
		t = 1 s	_	0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	_	500	mW
T <sub>stg</sub>	storage temperature		-65	+200	°C
Tj	junction temperature		_	200	°C

### Note

1. Device mounted on an FR4 printed-circuit board; lead length 10 mm.

### **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>F</sub>	forward voltage	see Fig.3			
	1N4148	I <sub>F</sub> = 10 mA	_	1	V
	1N4448	I <sub>F</sub> = 5 mA	0.62	0.72	V
		I <sub>F</sub> = 100 mA	_	1	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 20 V; see Fig.5		25	nA
		$V_R = 20 \text{ V}; T_j = 150 ^{\circ}\text{C}; \text{ see Fig.5}$	_	50	μΑ
I <sub>R</sub>	reverse current; 1N4448	$V_R = 20 \text{ V}; T_j = 100 ^{\circ}\text{C}; \text{ see Fig.5}$	_	3	μΑ
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0 V; see Fig.6	_	4	pF
t <sub>rr</sub>	reverse recovery time	when switched from $I_F$ = 10 mA to $I_R$ = 60 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 1 mA; see Fig.7	_	4	ns
V <sub>fr</sub>	forward recovery voltage	when switched from $I_F = 50$ mA; $t_r = 20$ ns; see Fig.8	_	2.5	V

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-tp)</sub>	thermal resistance from junction to tie-point	lead length 10 mm	240	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	lead length 10 mm; note 1	350	K/W

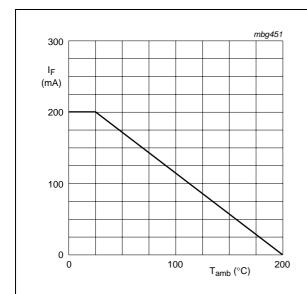
### Note

1. Device mounted on a printed-circuit board without metallization pad.

## High-speed diodes

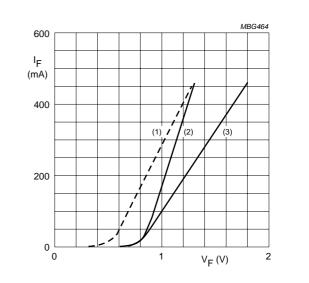
1N4148; 1N4448

### **GRAPHICAL DATA**



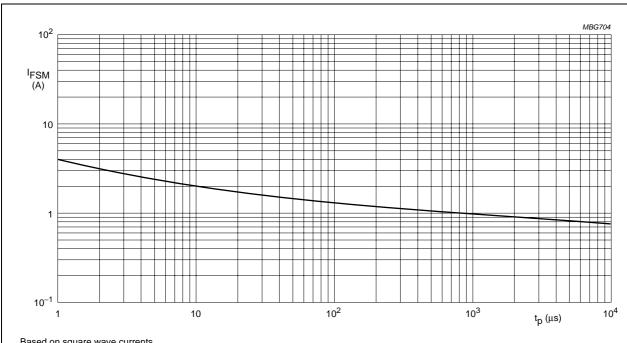
Device mounted on an FR4 printed-circuit board; lead length 10 mm.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1)  $T_j = 175$  °C; typical values.
- (2)  $T_j = 25$  °C; typical values.
- (3)  $T_j = 25$  °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



Based on square wave currents.

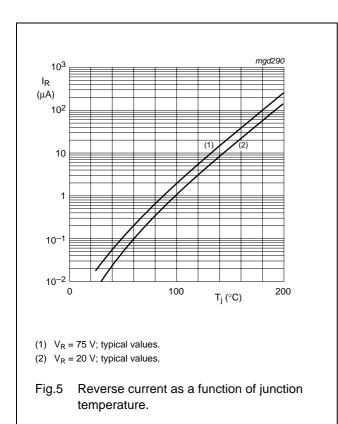
 $T_j = 25$  °C prior to surge.

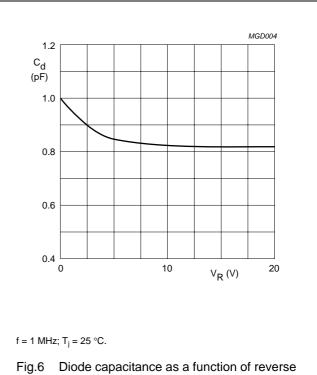
Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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# High-speed diodes

1N4148; 1N4448



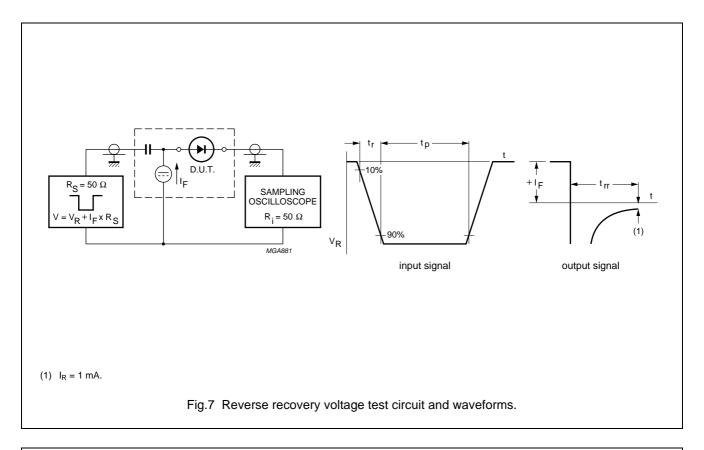


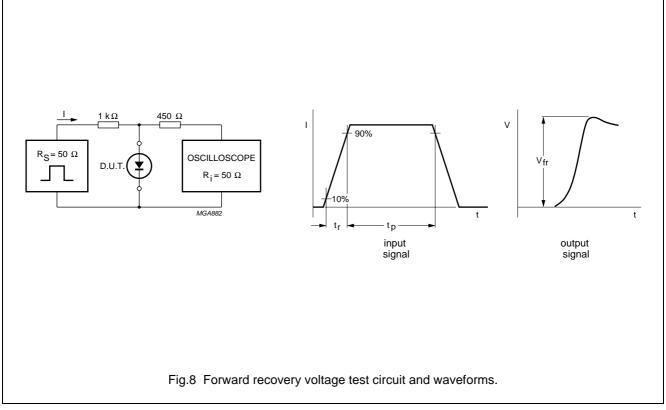
voltage; typical values.

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# High-speed diodes

1N4148; 1N4448





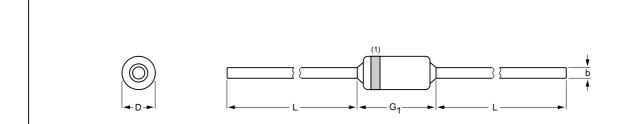
# High-speed diodes

1N4148; 1N4448

### **PACKAGE OUTLINE**

### Hermetically sealed glass package; axial leaded; 2 leads

SOD27



### **DIMENSIONS (mm are the original dimensions)**

UNIT	b	D	G <sub>1</sub>	L
	max.	max.	max.	min.
mm	0.56	1.85	4.25	25.4

0 1 2 mm scale

### Note

1. The marking band indicates the cathode.

OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION ISSUE DATE	
SOD27	A24	DO-35	SC-40			<del>97-06-09</del> 05-12-22

### High-speed diodes

1N4148; 1N4448

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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